

SG75N07Q 75V N-Channel Power MOSFET

 $\begin{array}{c} PDFN 5*6-8L \\ \hline PDFN 5*$

Description	Features
The SG75N07Q uses advanced Trench technology and designs to provide excellent $R_{\mbox{\tiny DS(ON)}}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.	 Low On-Resistance Low Input Capacitance Low Miller Charge Low Input/Output Leakage
	Applications
	 Motor / Body Load Control Load Switch DC-DC converters and Off-line UPS

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG75N07Q	Halogen-Free	PDFN 5*6-8L	Q	Tape & Reel	2,500

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Param	eter	Symbol	Value	Unit
Drain-Source Voltage		V _{DS}	75	V
Gate-Source Voltage		V _{GS}	±25	٧
Drain Current-Continuous Note 3	T _c =25°C		80	A
	$T_c = 70^{\circ}C$	I _D	64	A
Drain Current-Pulsed Note 1		I _{DM}	300	A
Desin Current Continuous	$T_A = 25^{\circ}C$		18	А
Drain Current-Continuous	$T_A = 70^{\circ}C$	ID	15	A
Avalanche Current, L=0.5mH		I _{AS}	28.3	А
Avalanche Energy, L=0.5mH		E _{AS}	200	mJ
	T _c =25°C		104	W
Maximum Dawar Dissinction	$T_c = 70^{\circ}C$		67	W
Maximum Power Dissipation	$T_A = 25^{\circ}C$	P _D	5.7	W
	$T_A = 70^{\circ}C$		3.6	W
Storage Temperature Range		T _{STG}	-55 to +150	0°
Operating Junction Temperature Range		Tj	-55 to +150	0°

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient Note 2	$R_{\theta_{JA}}$	Steady State	-	-	62	°C/W
Maximum Junction-to-Case Note 2	$R_{\theta_{JC}}$	Steady State	-	-	1.2	°C/W

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OFF CHARACTERISTICS

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	$V_{GS} = 0V, I_{DS} = 250 \mu A$	75	-	-	٧
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 60V, V_{GS} = 0V$	-	-	1	μA
Gate-Body Leakage	I _{GSS}	$V_{GS} = \pm 25V, V_{DS} = 0V$	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V _{gs(th)}	$V_{DS} = V_{GS}, I_{DS} = 250 \mu A$	2	3	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	$V_{GS} = 10V, I_{DS} = 30A$	-	7	9	mΩ

DYNAMIC CHARACTERISTICS

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	C _{iss}		-	4800	-	
Output Capacitance	C _{oss}	V_{DS} =30V, V_{GS} =0V, f=1MHz	-	650	-	pF
Reverse Transfer Capacitance	C _{rss}		-	340	-	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T _{d(on)}		-	25	-	
Rise Time	t _r	$V_{DD} = 30V, I_{D} = 30A, V_{Gs} = 10V,$	-	21	-	
Turn-Off Delay Time	T _{d(off)}	$Rg=3\Omega$	-	85	-	- ns
Fall Time	t _f		-	42	-	
Total Gate Charge at 10V	Q _g		-	125	-	
Gate to Source Gate Charge	Q _{gs}	V_{DS} =30V, I_{DS} =30A, V_{GS} =10V	-	35	-	nC
Gate to Drain "Miller" Charge	Q _{gd}		-	48	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Diode Forward Voltage	V _{SD}	$V_{GS} = 0V, I_{S} = 30A$	-	-	1.3	V
Body Diode Reverse Recovery Time	t _{rr}	L _ 201 dl/dt _ 1001/up	-	32	-	ns
Body Diode Reverse Recovery Charge	Q _{rr}	I _F =30A, dl/dt=100A/µs	-	47	-	nC

Notes:

1. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

2. $R_{\Theta_{JA}}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\Theta_{JC}}$ is guaranteed by design while $R_{\Theta_{CA}}$ is determined by the user's board design. $R_{\Theta_{JA}}$ shown below for single device operation on FR-4 in still air.

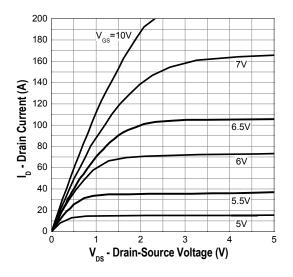
3. The maximum current rating is limited by package.

Typical Operating Characteristics

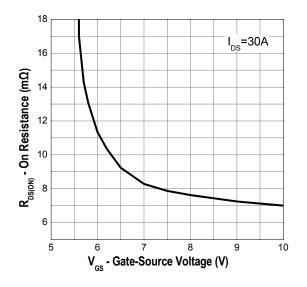


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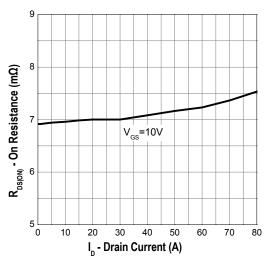
Output Characteristics



Gate-Source On Resistance



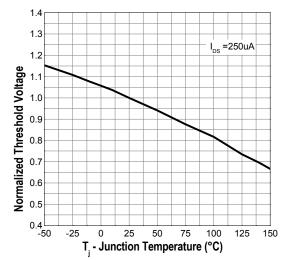
Drain-Source On Resistance



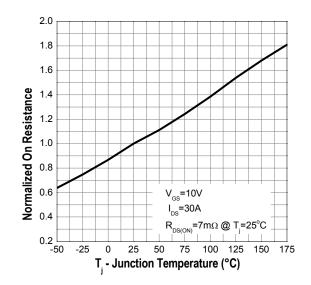
Typical Operating Characteristics (Cont.)

Power Dissipation

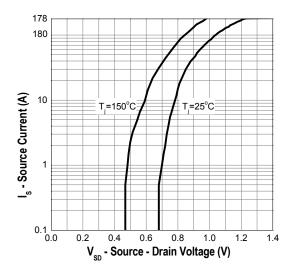
Gate Threshold Voltage



Drain-Source On Resistance



Source-Drain Diode Forward

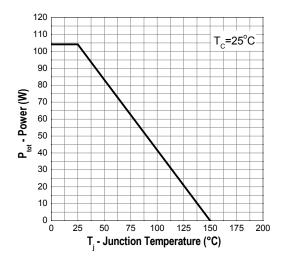


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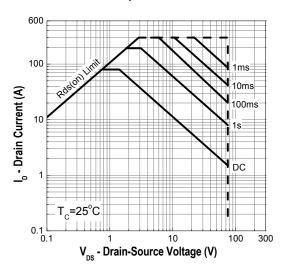
DS-SG75N07Q_04



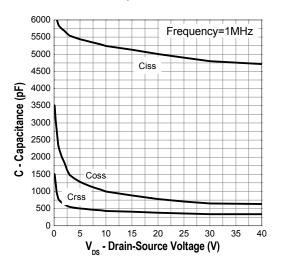
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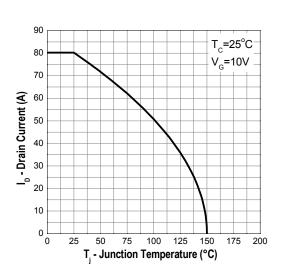
Safe Operation Area



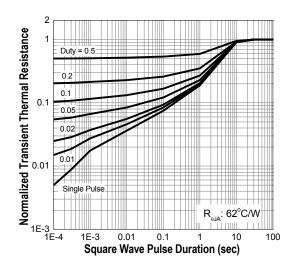
Capacitance



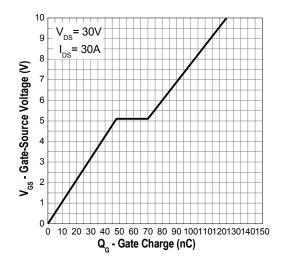
Outline Dimension



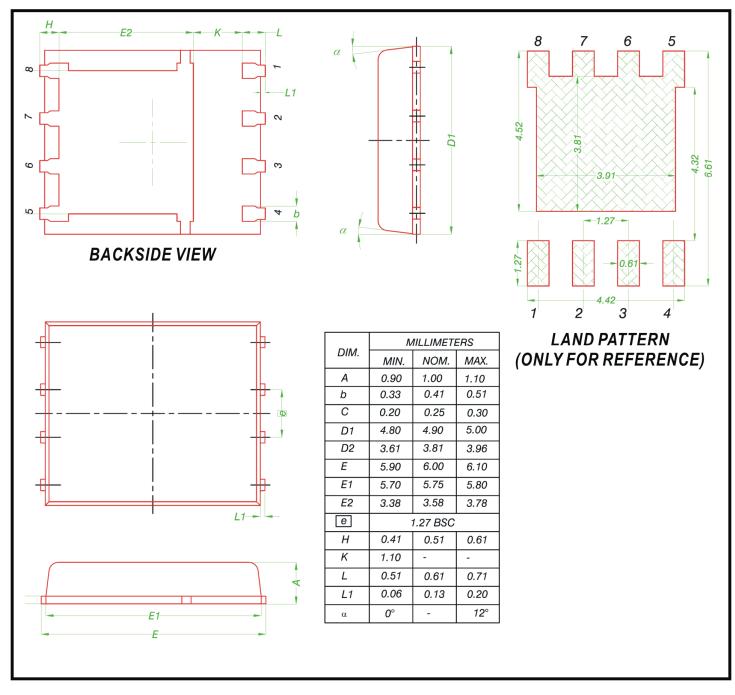
Transient Thermal Impedance



Gate Charge







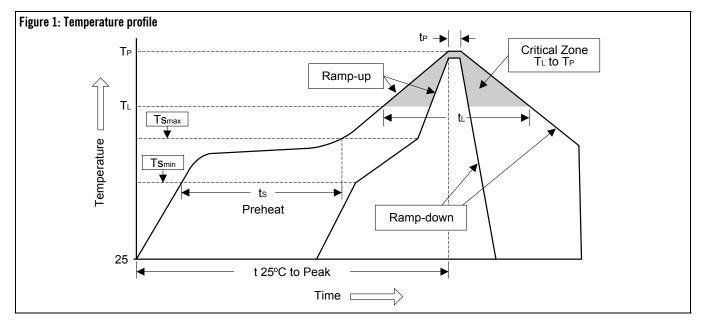
Note:

- 1. All Dimensions are in mm.
- 2. Package body sizes exclude Mold Flash, Protrusion or Gate Burrs. Mold Flash, Protrusion or Gate Burrs Shall not exceed 0.10mm per side.
- 3. Package body sizes determined at the outermost extremes of the plastic body exclusive of Mold Flash, Tie Bar, Tie Bar Burrs, Gate Burrs and Interlead Flash, But Including any mismatch between the top and bottom of the plastic body.
- 4. The package top may be smaller than the package bottom.

Soldering Methods for SiliconGear's Products



2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts _{min})	100°C	150°C
- Temperature Max (Ts _{max})	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T_L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T _L)	183°C	217°C
- Time (t _L)	60 to 150 sec	60 to 150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t_P)	10 10 50 500	20 10 40 360
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	$5 ext{sec} \pm 1 ext{sec}$



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